

SEMICONDUCTOR MEMORY DEVICE

ABSTRACT OF THE DISCLOSURE

The present disclosure relates to a semiconductor memory device. A
charge recycling circuit is driven to raise a potential of a restore node and a
5 sensing bar node to a given potential before a sensing operation is performed.
After the sensing operation is performed, electric charges discharged from the
restore node and from the sensing bar node are stored using the charge
recycling circuit and can then be used when a next sensing operation is
performed. Therefore, current consumed when the sensing operation is
10 performed can be reduced and the power consumption can be thus reduced.